

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	US-5640343-\$.DID. OR US-5650958-\$.DID. OR US-6385082-\$.DID. OR US-6538919-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 12:16
L2	15	(US-20020096775-\$ or US-20030011939-\$ or US-20030199104-\$ or US-20030206434-\$ or US-20040014245-\$ or US-20040084400-\$ or US-20040183099-\$ or US-20040188732-\$ or US-20050009212-\$).did. or (US-6518588-\$ or US-6689622-\$ or US-6707084-\$ or US-6806096-\$ or US-6815248-\$ or US-6897532-\$).did.	US-PGPUB; USPAT	OR	ON	2005/06/07 12:43
S1	67	(mtj or mram or magnetic near tunnel near junction or tmr) near6 (titanium or tantalum or tin or tan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 12:16
S2	50	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or hardmask or mask or masking) near8 (titanium or tin or ti near n) near8 (tantalum or tan or ta near n)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/01 14:59
S3	455	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near4 (lamine or lamination or laminated or stack or stacked or (plural or plurality or multi or multiple or bi or second or third or three) near2 (layer\$4 or level\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/01 15:48
S4	281	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near2 (lamine or lamination or laminated or stack or stacked or (plural or plurality or multi or multiple or bi or second or third or three) near2 (layer\$4 or level\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 08:32
S5	7	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near5 (titanium adj nitride or tin or ti near n) near5 (tantalum adj nitride or tan or ta near n) near5 (titanium or ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 08:30
S6	209	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near2 (bilayer\$2 or trilayer\$2 (plural or plurality or multi or multiple or bi or second or third or three) near2 (layer\$4 or level\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 10:30
S7	13	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near2 (oxidized or oxidizing or oxidation or oxide) near4 (side or wall or surface or outside or sidewall or edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 10:35
S8	26	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near2 (oxidized or oxidizing or oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 10:56
S9	38	(mtj or mram or magnetic near tunnel near junction or tmr) and (cap or capping or mask or masking or hardmask) near4 (oxide or oxidation) near4 (wall or side or sidewall or edge or surface or outside or outer or periphery or vertical)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:14
S10	1	(mtj or mram or magnetic near tunnel near junction or tmr) and (photoresist or resist) near4 (fence or fencing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:04

S11	13	(mtj or mram or magnetic near tunnel near junction or tnr) and (fence or fencing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:06
S12	23	(mtj or mram or magnetic near tunnel near junction or tnr) and (mask or hardmask or masking or cap or capping or photoresist or resist) near5 (redeposit\$4 or re-deposit\$4 or resputter\$4 or re-sputter\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:07
S13	87	(ferromagnet\$2 or pinning or pinned or afm) and (cap or capping or mask or masking or hardmask) near3 (oxide or oxidation or oxidizing or oxidized) near3 (wall or side or sidewall or edge or surface or outside or outer or periphery or vertical)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:19
S14	14	(ferromagnet\$2 or pinning or pinned or afm or mtj or mram or tnr) and (cap or capping or mask or masking or hardmask) near4 (partial or partially or mostly or majority or most or incomplete or incompletely or partway or halfway) near3 (etching or etched or etch or removal or removing or removed or strip or stripping or stripped) near4 (resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:21
S15	124	(ferromagnet\$2 or pinning or pinned or afm or mtj or mram or tnr) and (cap or capping or mask or masking or hardmask) near4 (etching or etched or etch) near4 (removal or removing or removed or strip or stripping or stripped) near4 (resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:23
S16	51	(mtj or mram or tnr) and (cap or capping or mask or masking or hardmask) near4 (etching or etched or etch) near4 (removal or removing or removed or strip or stripping or stripped) near4 (resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:30
S17	915	438/3.ccor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:30
S18	117	438/3.ccor. and (cap or capping or hardmask or mask or masking) near10 (tan or tin or tantalum or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:34
S19	1	438/736.ccor. and (mram or mtj or tnr or ferromagnet\$2 or cofe or nife)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:35
S20	1	438/738.ccor. and (mram or mtj or tnr or ferromagnet\$2 or cofe or nife)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:36
S21	1	438/738.ccor. and (tantalum adj nitride or tan or ta adj n) near3 (titanium or ti) near3 (titanium adj nitride or tin or ti adj n)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/02 11:40